

# Andrea Edit Pap

## List of Publications by Year in descending order

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Version: 2024-02-01

12  
papers

322  
citations

1040056

9  
h-index

1199594

12  
g-index

12  
all docs

12  
docs citations

12  
times ranked

451  
citing authors

#	ARTICLE	IF	CITATIONS
1	Optical properties of porous silicon. Part III: Comparison of experimental and theoretical results. <i>Optical Materials</i> , 2006, 28, 506-513.	3.6	81
2	Thermal Oxidation of Porous Silicon: A Study on Reaction Kinetics. <i>Journal of Physical Chemistry B</i> , 2004, 108, 12744-12747.	2.6	60
3	Optical properties of porous silicon.. <i>Optical Materials</i> , 2004, 25, 257-260.	3.6	28
4	Simultaneous chemical silver and palladium deposition on porous silicon; FESEM, TEM, EDX and XRD investigation. <i>Applied Surface Science</i> , 2002, 201, 56-60.	6.1	27
5	Optical properties of porous silicon.. <i>Optical Materials</i> , 2004, 25, 251-255.	3.6	26
6	Reference-free quantification of particle-like surface contaminations by grazing incidence X-ray fluorescence analysis. <i>Journal of Analytical Atomic Spectrometry</i> , 2012, 27, 248-255.	3.0	24
7	Fine-tuning of gas sensitivity by modification of nano-crystalline WO <sub>3</sub> layer morphology. <i>Sensors and Actuators B: Chemical</i> , 2015, 221, 281-289.	7.8	24
8	WO <sub>3</sub> nano-rods sensitized with noble metal nano-particles for H <sub>2</sub> S sensing in the ppb range. <i>Materials Research Bulletin</i> , 2016, 84, 480-485.	5.2	23
9	Thermo-mechanical design and characterization of low dissipation micro-hotplates operated above 500°C. <i>Microelectronics Journal</i> , 2014, 45, 1822-1828.	2.0	17
10	Probing Patterned Wafer Structures by Means of Grazing Incidence X-ray Fluorescence Analysis. <i>ECS Transactions</i> , 2009, 25, 441-451.	0.5	6
11	Origin and FEM-assisted evaluation of residual stress in thermally oxidized porous silicon. <i>Computational Materials Science</i> , 2005, 34, 123-128.	3.0	4
12	Nano-structured WO <sub>3</sub> layers sensitized with ALD Pt for quick detection of H <sub>2</sub> S. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 17148-17155.	2.2	2